

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Canceled).

Claim 2 (Currently Amended): The composite substrate of claim ~~[[1]] 26~~<sup>1</sup>, wherein said substrate is composed mainly of magnesia (MgO), steatite (MgO·SiO<sub>2</sub>) or forsterite (2MgO·SiO<sub>2</sub>).

Claims 3-5 (Canceled).

~~Claim 6~~<sup>3</sup> (Currently Amended): The composite substrate of claim ~~[[3]] 26~~<sup>1</sup>, wherein said dielectric layer contains a vitreous component composed of silicon oxide (SiO<sub>2</sub>).

~~Claim 7~~<sup>11</sup> (Currently Amended): An EL device comprising at least a light emitting layer and a second electrode on the composite substrate of claim ~~[[1]] 26~~<sup>1</sup>.

~~Claim 8~~<sup>12</sup> (Original): The EL device of claim ~~7~~<sup>11</sup> further comprising a second insulator layer between the light emitting layer and the second electrode.

Claim 9 (Currently Amended): The composite substrate of claim ~~[[1]] 26~~<sup>1</sup>, wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate (BaTiO<sub>3</sub>).

<sup>4</sup>  
~~Claim 10~~ (Currently Amended): The composite substrate of claim ~~[[1]] 26~~<sup>1</sup>, wherein said substrate has a coefficient of thermal expansion of about 12 to 18 ppm/K.

<sup>10</sup>  
~~Claim 11~~ (Previously Presented): The composite substrate of claim 2, wherein said substrate is composed mainly of magnesia.

<sup>5</sup>  
~~Claim 12~~ (Currently Amended): The composite substrate of claim ~~[[1]] 26~~<sup>1</sup>, wherein the electrode comprises a metallic electrode selected from the group consisting of palladium, rhodium, iridium, rhenium, ruthenium, platinum, silver, gold, tantalum, nickel, chromium and titanium.

<sup>6</sup>  
~~Claim 13~~ (Currently Amended): The composite substrate of claim ~~[[1]] 26~~<sup>1</sup>, wherein the electrode comprises a metallic electrode selected from the group consisting of Pd, Pt, Au, Ag and an alloy thereof.

<sup>13</sup>  
~~Claim 14~~ (Previously Presented): The EL device of claim ~~7~~<sup>11</sup>, wherein the second electrode is a transparent electrode of ITO or IZO.

<sup>14</sup>  
~~Claim 15~~ (Previously Presented): The EL device of claim ~~14~~<sup>13</sup>, wherein said ITO comprises a proportion of SnO<sub>2</sub> to In<sub>2</sub>O<sub>3</sub> of from 1 to 20% by weight.

<sup>15</sup>  
~~Claim 16~~ (Previously Presented): The EL device of claim ~~14~~<sup>13</sup>, wherein said IZO comprises a proportion of ZnO to In<sub>2</sub>O<sub>3</sub> of about 12 to 32% by weight.

Claim ~~17~~<sup>16</sup> (Previously Presented): The EL device of claim ~~14~~<sup>13</sup>, wherein the second electrode is silicon-based.

Claim ~~18~~<sup>17</sup> (Previously Presented): The EL device of claim ~~17~~<sup>16</sup>, wherein the silicon-based electrode is selected from the group consisting of polycrystalline silicon (p-Si), amorphous silicon (a-Si) and single crystal silicon.

Claim ~~19~~<sup>18</sup> (Previously Presented): The EL device of claim ~~17~~<sup>16</sup>, wherein said silicon-based electrode comprises a dopant to impart conductivity.

Claim ~~20~~<sup>19</sup> (Previously Presented): The EL device of claim ~~19~~<sup>18</sup>, wherein said dopant is selected from the group consisting of B, P, As, Sb and Al in an amount of about 0.001 to 5 at. %.

Claim ~~21~~<sup>20</sup> (Previously Presented): The EL device of claim ~~14~~<sup>13</sup>, wherein said second electrode has a resistivity of up to 1  $\Omega\cdot\text{cm}$ .

Claim ~~22~~<sup>21</sup> (Previously Presented): The EL device of claim ~~21~~<sup>20</sup>, wherein said second electrode has a resistivity of from about 0.003 to 0.1  $\Omega\cdot\text{cm}$ .

Claim ~~23~~<sup>22</sup> (Previously Presented): The EL device of claim ~~7~~<sup>11</sup>, wherein said light emitting layer comprises a phosphor.

<sup>23</sup>  
Claim ~~24~~ (Previously Presented): The EL device of claim ~~23~~<sup>22</sup>, wherein said phosphor is a sulfide phosphor.

<sup>24</sup>  
Claim ~~25~~ (Previously Presented): The EL device of claim ~~24~~<sup>23</sup>, wherein said sulfide phosphor is a ZnS phosphor.

~~Claim 26~~ (New): A composite substrate in which an electrode and a dielectric layer are successively formed on an electrically insulating substrate,  
said substrate having a coefficient of thermal expansion of 10 to 20 ppm/K,  
wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate ( $\text{BaTiO}_3$ ), and  
wherein said dielectric layer contains one or more oxides selected from the group consisting of manganese oxide ( $\text{MnO}$ ), magnesium oxide ( $\text{MgO}$ ), tungsten oxide ( $\text{WO}_3$ ), calcium oxide ( $\text{CaO}$ ), zirconium oxide ( $\text{ZrO}_2$ ), niobium oxide ( $\text{Nb}_2\text{O}_5$ ) and cobalt oxide ( $\text{Co}_2\text{O}_3$ ).

<sup>25</sup>  
~~Claim 27~~ (New): A composite substrate in which an electrode and a dielectric layer are successively formed on an electrically insulating substrate,  
said substrate having a coefficient of thermal expansion of 10 to 20 ppm/K,  
wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate ( $\text{BaTiO}_3$ ), and  
wherein said dielectric layer contains the oxides of one or more elements selected from the group consisting of rare earth elements Sc, Y, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu.

~~34~~  
Claim ~~28~~ (New): An EL device comprising at least a light emitting layer and a second electrode on the composite substrate of claim ~~27~~. ~~25~~

~~35~~ ~~34~~  
Claim ~~29~~ (New): The EL device of claim ~~28~~ further comprising a second insulator layer between the light emitting layer and the second electrode.

Claim 30 (New): The composite substrate of claim 27, wherein said dielectric layer is a sintered ceramic body composed mainly of barium titanate ( $\text{BaTiO}_3$ ).

~~26~~ ~~25~~  
Claim ~~31~~ (New): The composite substrate of claim ~~27~~, wherein said substrate has a coefficient of thermal expansion of about 12 to 18 ppm/K.

~~27~~ ~~25~~  
Claim ~~32~~ (New): The composite substrate of claim ~~27~~, wherein the electrode comprises a metallic electrode selected from the group consisting of palladium, rhodium, iridium, rhenium, ruthenium, platinum, silver, gold, tantalum, nickel, chromium and titanium.

~~28~~ ~~25~~  
Claim ~~33~~ (New): The composite substrate of claim ~~27~~, wherein the electrode comprises a metallic electrode selected from the group consisting of Pd, Pt, Au, Ag and an alloy thereof.

~~36~~ ~~34~~  
Claim ~~34~~ (New): The EL device of claim ~~28~~, wherein the second electrode is a transparent electrode of ITO or IZO.

~~37~~  
Claim ~~35~~ (New): The EL device of claim ~~34~~, wherein said ITO comprises a proportion of  $\text{SnO}_2$  to  $\text{In}_2\text{O}_3$  of from 1 to 20% by weight.

~~38~~  
Claim ~~36~~ (New): The EL device of claim ~~34~~, wherein said IZO comprises a proportion of  $\text{ZnO}$  to  $\text{In}_2\text{O}_3$  of about 12 to 32% by weight.

~~39~~  
Claim ~~37~~ (New): The EL device of claim ~~34~~, wherein the second electrode is silicon-based.

~~42~~  
Claim ~~38~~ (New): The EL device of claim ~~37~~, wherein the silicon-based electrode is selected from the group consisting of polycrystalline silicon (p-Si), amorphous silicon (a-Si) and single crystal silicon.

~~43~~  
Claim ~~39~~ (New): The EL device of claim ~~37~~, wherein said silicon-based electrode comprises a dopant to impart conductivity.

~~44~~  
Claim ~~40~~ (New): The EL device of claim ~~39~~, wherein said dopant is selected from the group consisting of B, P, As, Sb and Al in an amount of about 0.001 to 5 at.%.

~~40~~  
Claim ~~41~~ (New): The EL device of claim ~~34~~, wherein said second electrode has a resistivity of up to  $1 \Omega \cdot \text{cm}$ .

~~46~~  
Claim ~~42~~ (New): The EL device of claim ~~41~~, wherein said second electrode has a resistivity of from about 0.003 to  $0.1 \Omega \cdot \text{cm}$ .

~~45~~ ~~34~~  
Claim ~~43~~ (New): The EL device of claim ~~28~~, wherein said light emitting layer comprises a phosphor.

~~46~~ ~~45~~  
Claim ~~44~~ (New): The EL device of claim ~~43~~, wherein said phosphor is a sulfide phosphor.

~~47~~ ~~46~~  
Claim ~~45~~ (New): The EL device of claim ~~44~~, wherein said sulfide phosphor is a ZnS phosphor.

~~7~~ ~~1~~  
Claim ~~46~~ (New): The composite substrate of claim ~~26~~, wherein said one or more oxides are present in an amount of up to 50 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

~~8~~ ~~1~~  
Claim ~~47~~ (New): The composite substrate of claim ~~26~~, wherein said one or more oxides are present in an amount of 0.004 to 40 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

~~9~~ ~~1~~  
Claim ~~48~~ (New): The composite substrate of claim ~~26~~, wherein said one or more oxides are present in an amount of 0.01 to 30 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

~~29~~ ~~25~~  
Claim ~~49~~ (New): The composite substrate of claim ~~27~~, wherein said oxides of one or more elements are present in an amount of up to 50 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

<sup>30</sup>  
Claim ~~50~~ (New): The composite substrate of claim <sup>25</sup>~~27~~, wherein said oxides of one or more elements are present in an amount of 0.004 to 40 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

<sup>31</sup>  
Claim ~~51~~ (New): The composite substrate of claim <sup>25</sup>~~27~~, where said oxides of one or more elements are present in an amount of 0.01 to 30 mol%, based on barium titanate ( $\text{BaTiO}_3$ ).

<sup>32</sup>  
Claim ~~52~~ (New): The composite substrate of claim <sup>25</sup>~~27~~, wherein said substrate is composed mainly of magnesia ( $\text{MgO}$ ), steatite ( $\text{MgO} \cdot \text{SiO}_2$ ) or forsterite ( $2\text{MgO} \cdot \text{SiO}_2$ ).

<sup>33</sup>  
Claim ~~53~~ (New): The composite substrate of claim <sup>25</sup>~~27~~, wherein said substrate is composed mainly of magnesia.